

**IN THE CLAIMS**

Please cancel claims 1-3, 11-13, 23 and 24 without prejudice or disclaimer of their subject matter, amend claims 4, 5, 9, 14, 15, 19, 21, 25 and 26 as follows:

Claims 1-3. (Canceled)

1           4. (Currently Amended)   [[The]] A thin film transistor of claim 3, comprising a  
2           source electrode, a drain electrode, a gate electrode, and a semiconductor layer;  
3           wherein one of the source electrode, the drain electrode, and the gate electrode  
4           comprises an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer  
5           interposed between the titanium and the aluminum-based layers;  
6           wherein the diffusion prevention layer is a titanium nitride layer; and  
7           wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1           5. (Currently Amended) The thin film transistor of claim [[3]] 4, wherein the  
2           titanium nitride layer has a thickness of about 100 to 600Å.

1           6. (Original) The thin film transistor of claim 5, wherein the titanium nitride layer  
2           has a thickness of about 100 to 400Å.

1           7. (Original) The thin film transistor of claim 6, wherein the titanium nitride layer  
2           has a thickness of 200 to 400Å.

1           8. (Original) The thin film transistor of claim 7, wherein the titanium nitride layer  
2           has a thickness of about 300Å.

1           9. (Currently Amended)   [[The]] A thin film transistor of claim 1, comprising a  
2           source electrode, a drain electrode, a gate electrode, and a semiconductor layer, wherein one  
3           of the source electrode, the drain electrode, and the gate electrode comprises an  
4           aluminum-based metal layer, a titanium layer, and a diffusion prevention layer interposed  
5           between the titanium and the aluminum-based layers, and wherein the aluminum-based metal  
6           layer is made of an aluminum alloy containing about 0.5 to 5 wt% of one element being  
7           selected from the group consisting of silicon, copper, neodymium, platinum, and nickel.

1           10. (Original) The thin film transistor of claim 9, wherein the aluminum-based metal  
2           layer is made of an aluminum-silicon alloy containing about 2 wt% of silicon.

Claims 11-13. (Canceled)

1           14. (Original)   [[The]] A flat panel display of claim 13, comprising a plurality of  
2           sub-pixels driven by thin film transistors, each of the thin film transistors comprising a  
3           source electrode, a drain electrode, a gate electrode, and a semiconductor layer;  
4           wherein at least one of the source electrode, the drain electrode, and the gate electrode  
5           comprises an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer  
6           interposed between the aluminum-based metal layer and the titanium layer;  
7           wherein the diffusion prevention layer is a titanium nitride layer; and

8 wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1 15. (Currently Amended) The flat panel display of claim ~~[[13]]~~ 14, wherein the  
2 titanium nitride layer has a thickness of about 100 to 600Å.

1 16. (Original) The flat panel display of claim 15, wherein the titanium nitride layer  
2 has a thickness of about 100 to 400Å.

1 17. (Original) The flat panel display of claim 16, wherein the titanium nitride layer  
2 has a thickness of 200 to 400Å.

1 18. (Original) The flat panel display of claim 17, wherein the titanium nitride layer  
2 has a thickness of about 300Å.

1 19. (Currently Amended) ~~[[The]]~~ A flat panel display of claim 11, comprising a  
2 plurality of sub-pixels driven by thin film transistors, each of the thin film transistors  
3 comprising a source electrode, a drain electrode, a gate electrode, and a semiconductor layer,  
4 wherein at least one of the source electrode, the drain electrode, and the gate electrode  
5 comprises an aluminum-based metal layer, a titanium layer, and a diffusion prevention layer  
6 interposed between the aluminum-based metal layer and the titanium layer, and wherein the  
7 aluminum-based metal layer is made of an aluminum alloy containing about 0.5 to 5 wt% of  
8 one element being selected from the group consisting of silicon, copper, neodymium,  
9 platinum, and nickel.

1           20. (Original) The flat panel display of claim 19, wherein the aluminum-based metal  
2 layer is made of an aluminum-silicon alloy containing about 2 wt% of silicon.

1           21. (Currently Amended) A flat panel display, comprising:  
2 driving circuits disposed along edges of said display;  
3 a plurality of sub-pixels driven by thin film transistors; and  
4 conductive lines connecting the driving circuits disposed along edges of said display  
5 to each of said plurality of sub-pixels, wherein said conductive lines comprise an  
6 aluminum-based metal layer, a titanium layer, and a diffusion prevention layer interposed  
7 between the aluminum-based metal layer and the titanium layer;  
8 wherein the diffusion prevention layer is a titanium nitride layer; and  
9 wherein said titanium nitride layer is 300 Å thick.

10          22. (Original) The flat panel display of claim 21, wherein the diffusion prevention  
11 layer and the titanium layer are orderly formed on opposite sides of the aluminum-based  
12 metal layer.

Claims 23-24. (Canceled)

1           25. (Currently Amended) The display of claim ~~[[24]]~~ 22, said conductive lines being  
2 subjected to a heat treatment of 380°C.

1           26. (Currently Amended) A process for making a flat panel display, comprising:  
2           disposing driving circuits along edges of said display;  
3           arranging a plurality of sub-pixels driven by thin film transistors; and  
4           operatively connecting electrically conductive lines between the driving circuits  
5           disposed along edges of said display and each of said plurality of sub-pixels, wherein said  
6           conductive lines comprise an aluminum-based metal layer, a titanium layer, and a diffusion  
7           prevention layer interposed between the aluminum-based metal layer and the titanium layer;  
8           wherein the titanium nitride layer contains 5 to 85 wt% of nitrogen.

1           27. (Previously Presented) The process of claim 26, comprised of orderly forming  
2           the diffusion prevention layer and the titanium layer on opposite sides of the  
3           aluminum-based metal layer.

1           28. (Previously Presented) The process of claim 26, wherein the diffusion prevention  
2           layer is a titanium nitride layer.